

/ Descriptions

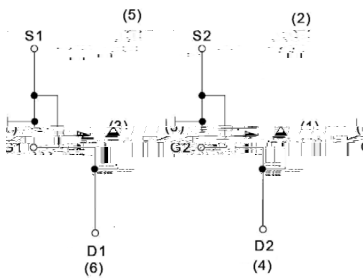
SOT23-6 P MOS
 Dual P-Channel MOSFET in a SOT23-6 Plastic Package.

/ Features

Super high dense cell design for low $R_{DS(ON)}$, Rugged and reliable. HF product.

/ Applications

Power Management in Notebook computer, Portable Equipment and Battery powered systems.

/ Equivalent Circuit**/ Pinning**

PIN1 G1 PIN 2 S2 PIN 3 G2

PIN 4 D2 PIN 5 S1 PIN 6 D1

/ Marking

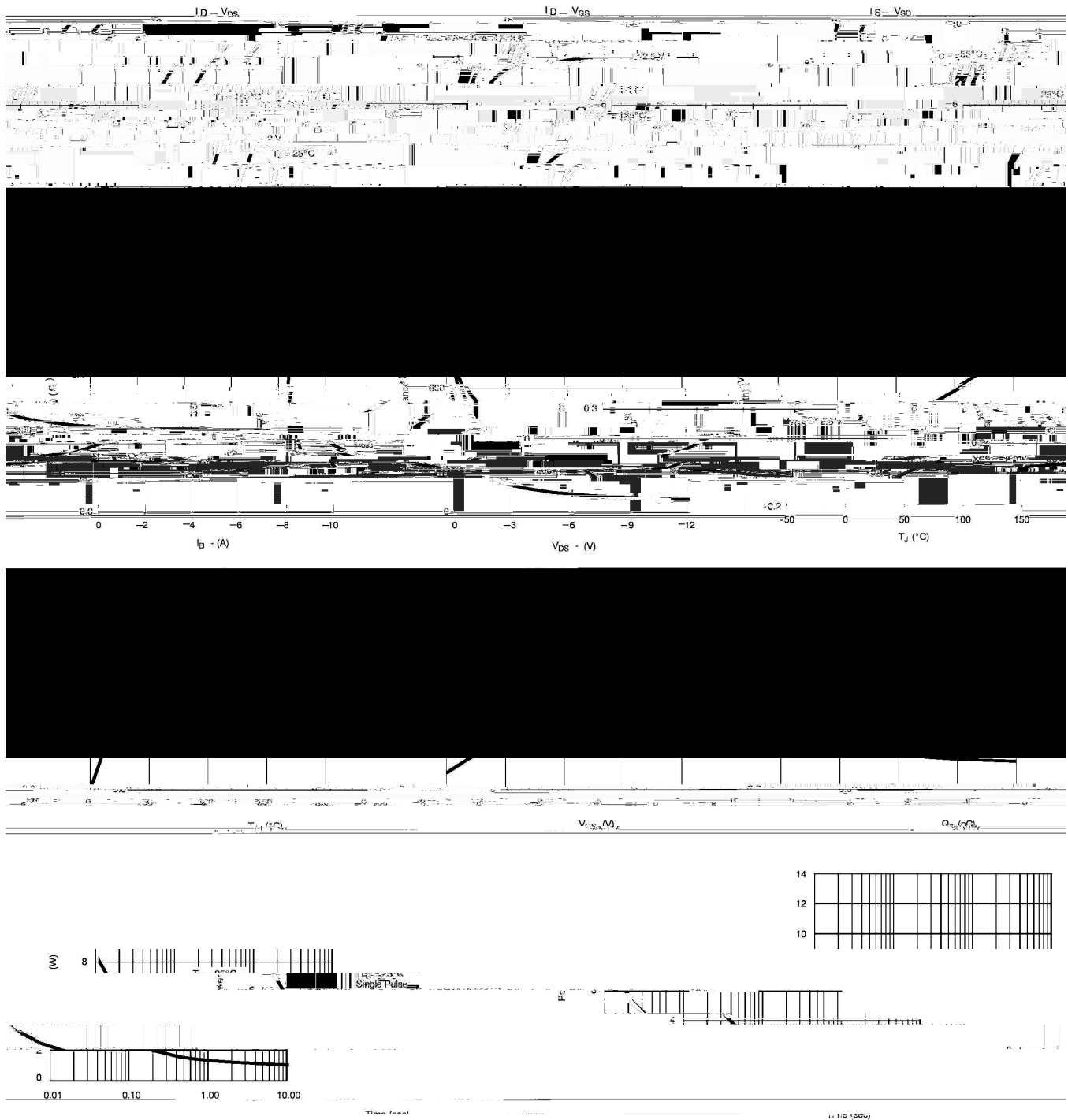
See Marking Instructions

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	-20	V
Gate-Source Voltage	V_{GSS}	± 12	V
Continuous Drain Current	I_D^*	-3.0	A

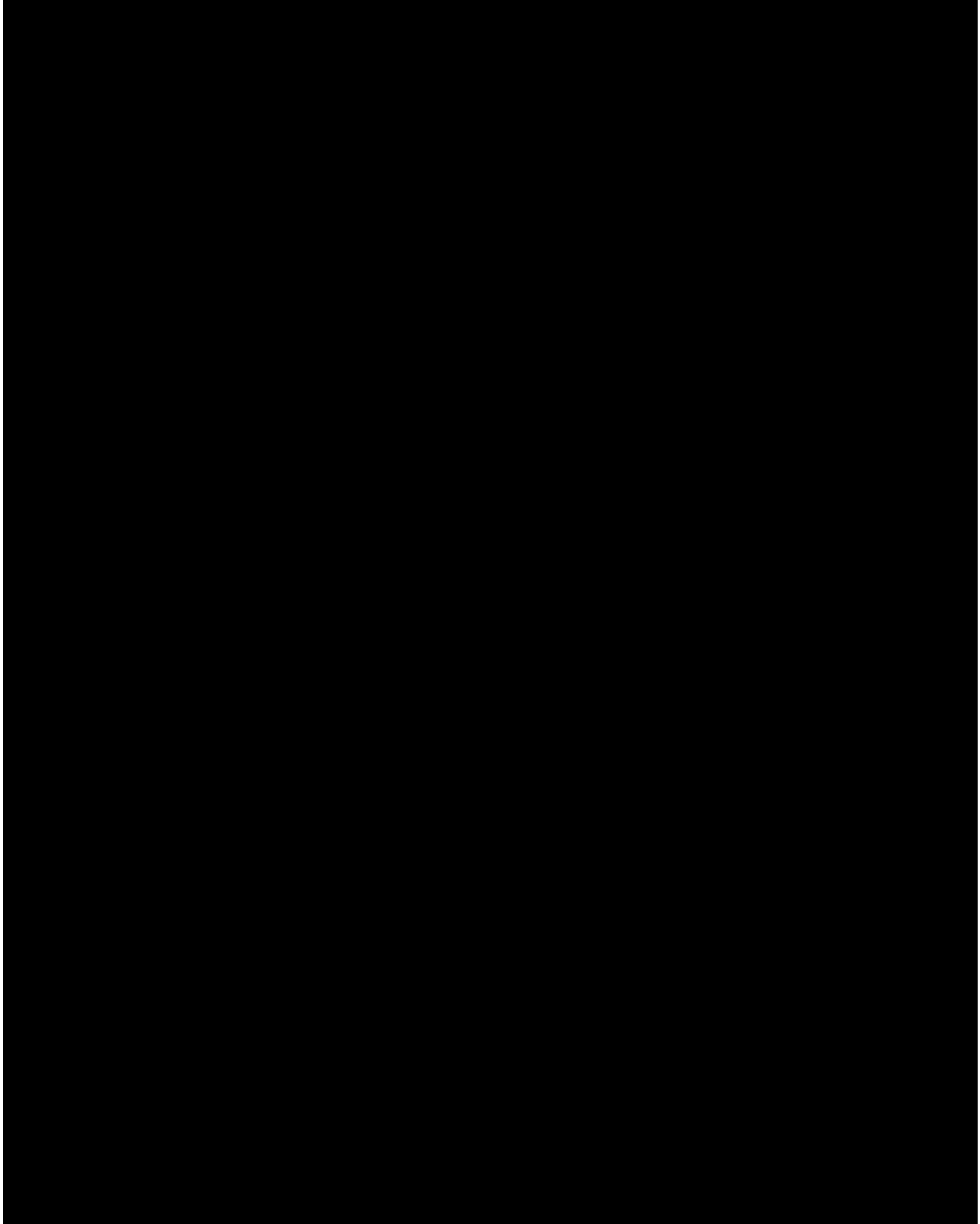
/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ
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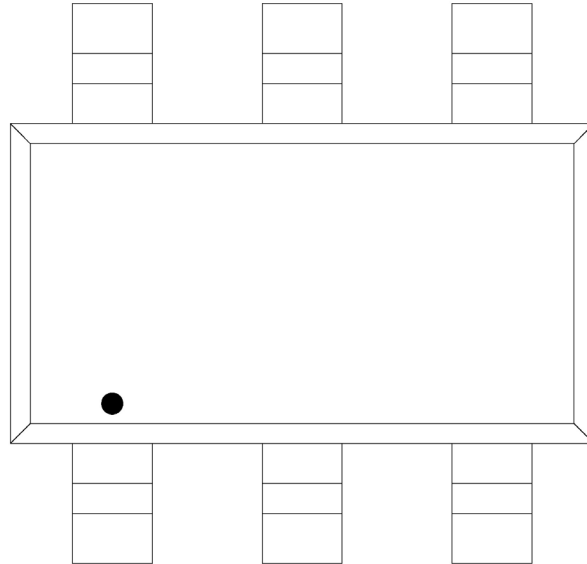
/ Electrical Characteristic Curve



/ Package Dimensions

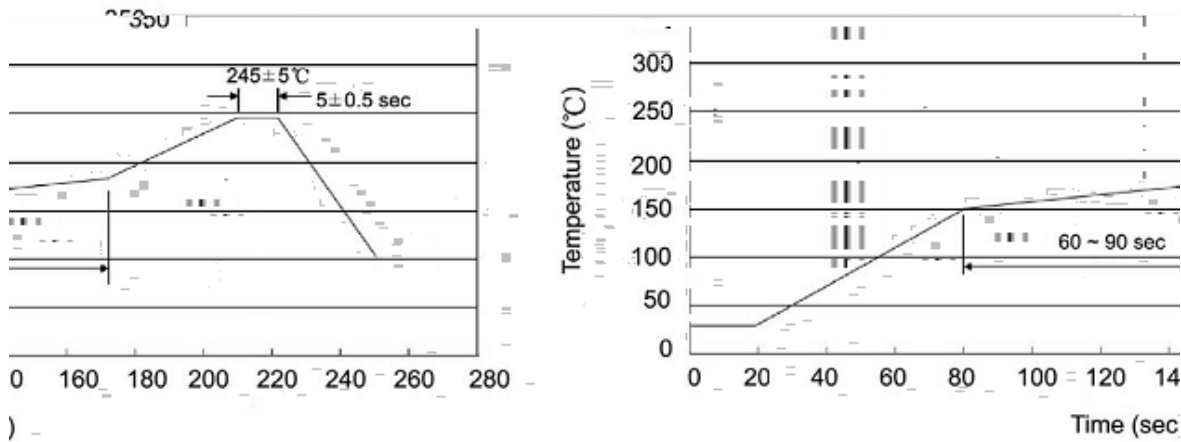


/ Marking Instructions



4953D

() / Whp shrdwxrh Prr iioh i rr IU Uhi orw Vroghriq j +Pe-Frhh,



- 1 150 180 60 90sec;
2 245±5 5±0.5sec;
3 2 10 /sec.

- Note:
1.Preheating:150~180 , Time:60~90sec.
2.Peak Temp.:245±5 , Duration:5±0.5sec.
3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

260±5 10±1 sec. Temp.:260±5 Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)	
封装形式	只	卷盘	卷盘盒	只盒	盒箱	只箱	盒箱